

<b>INFORMATION DISCLOSURE STATEMENT</b>	Atty. Docket No.: 150.01170103	Serial No.: 10/669,384
	Applicant(s): Basceri et al.	Confirmation No.: Unassigned
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## U.S. PATENT DOCUMENTS

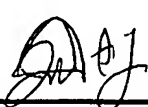
Examiner Initial	Copy Enclosed	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
HP		5,270,241	12/14/93	Dennison et al.	437	52	3/13/1992
HP		5,555,486	09/10/96	Kington et al.	361	305	12/29/1994
HP		6,117,689	09/12/00	Summerfelt	438	3	12/24/1997
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HP		6,337,239	01/08/02	Dehm et al.	438	240	9/8/1999
HP		6,372,291	04/16/02	Hua et al.	427	255.28	12/23/1999
HP		6,482,736	11/19/02	Basceri et al.	438	650	6/8/2000
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## FOREIGN PATENT DOCUMENTS

Examiner Initial	Copy Enclosed	Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
		None						

## OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)

Examiner Initial	Copy Enclosed	Document Description
HP	X	McGuire, "Semiconductor Materials and Process Technology Handbook," Noyes Publ., Nowich, NY, 1988: 291.
HP	X	Oh et al., "Thermal Stability of RuO <sub>2</sub> /Ru Bilayer Thin Film in Oxygen Atmosphere," <i>Thin Solid Films</i> , 2000;359: 118-123.
HP		Yoon et al., "Investigation of RuO <sub>2</sub> - Incorporated PT layer as a Bottom Electrode and Diffusion Barrier for High Epsilon Capacitor Applications," <i>Electrochem. and Solid-State Lett.</i> , 2000;3(8):373-376.

EXAMINER 	Date Considered 10/16/2005
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	